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Amendments to the Claims

Please amend the claims as shown below. This listing of Claims replaces all prior versions and listings of the claims in this application.

Listing of Claims

1. (Currently Amended) A method for fabricating an RF semiconductor device comprising:

the step of forming a trench to define an active region and an element isolation region in a semiconductor substrate;

the step of forming a plurality of gate lines within the active region of the semiconductor substrate, the plurality of gate lines not extending over a center of the trench;

the step of forming an insulating layer on the plurality of gate lines and the semiconductor substrate;

only one contact-hole-forming step which consists of the step of forming at least one contact hole in the insulating layer within the active region without forming [[a]] said at least one contact hole within the element isolation region;

the step of forming a contact plug in ~~the~~ each of said at least one contact hole; and

the step of forming a conductive pattern layer that is electrically connected with the contact plug.

2. (Previously Presented) A method as defined in claim 1, wherein the gate lines in the plurality are not connected with each other in the element isolation region.

3. (Previously Presented) A method as defined in claim 1, wherein at least two of the plurality of gate lines are connected in the active region.

4. (Original) A method as defined in claim 1, wherein a thickness of the insulating layer is about 1000 to about 20000 angstroms.

5. (Original) A method as defined in claim 1, wherein a thickness of the conductive pattern layer is above 10000 angstroms.

6. (Previously Presented) A method as defined in claim 1, wherein the insulating layer is one of an oxide and a polyimide.

7. (Previously Presented) A method as defined in claim 1, wherein the plurality of gate lines are formed in order to minimize parasitic capacitance between the plurality of gate lines and the substrate.

8. (Previously Presented) A method as defined in claim 1, wherein the plurality of gate lines are formed in order to minimize resistance of the plurality of gate lines.

9. (Previously Presented) A method as defined in claim 1, further comprising metal contacts linking at least two of the plurality of gate lines.

10. (Previously Presented) A method as defined in claim 1, wherein the plurality of gate lines do not extend along a longitudinal axis of the trench.

11-14. (Canceled)